TEXAS INSTRUMENTS
TLV9051-Q1, TLV9052-Q1
JAJSTB3B – FEBRUARY 2024 – REVISED MAY 2024

# TLV905x-Q1 車載、5MHz、15V/µs、高スルーレート、RRIO、CMOS オペアンプ

## 1 特長

- 車載アプリケーション用に AEC-Q100 認定済み:
  - 温度:-40℃～125℃、$T_A$
- 高いスルーレート:15V/µs
- 低い静止電流:330µA
- レール ツー レール入出力
- 低い入力オフセット電圧:±0.33mV
- ユニティ ゲイン帯域幅:5MHz
- 低い広帯域ノイズ:15nV/√Hz
- 低い入力バイアス電流:2pA
- ユニティ ゲイン安定
- 内部 RFI および EMI フィルタ
- 低コストのアプリケーション向けのスケーラブルな CMOS オペアンプ ファミリ
- 最低 1.8V の電源電圧で動作

## 2 アプリケーション

- AEC-Q100 グレード 1 アプリケーションに最適化
- HEV/EV のトラクション インバータおよびモータ制御
- HEV/EV の DC/DC コンバータ
- HEV/EV のバッテリ管理システム (BMS)
- オンボード チャージャ (OBC) およびワイヤレス チャージャ
- 車載各種ボディ モーター
- 車載のエアコン (冷暖房)

## 3 概要

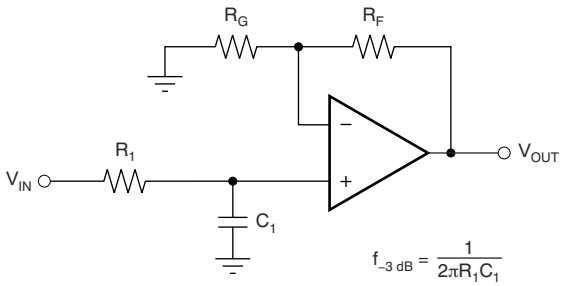
TLV9051-Q1、TLV9052-Q1、TLV9054-Q1 デバイスは、それぞれシングル、デュアル、クワッドのオペアンプです。これらのデバイスは 1.8V～6.0V の低電圧で動作するよう設計されています。入力と出力は、非常に高いスルー レートでレール ツー レール動作が可能です。これらのデバイスは、コストが制限され、低電圧動作、高いスルー レート、小さい静止電流が要求されるアプリケーションに理想的です。TLV905x-Q1 ファミリの容量性負荷の駆動能力は 150pF であり、オープン ループ出力インピーダンスが抵抗性なので、はるかに大きな容量性負荷についても容易に安定化できます。

TLV905x-Q1 ファミリのデバイスはユニティ ゲイン安定で、RFI および EMI フィルタが内蔵され、オーバードライブ状況でも位相反転が発生しないため、簡単に使用できます。

**製品情報**

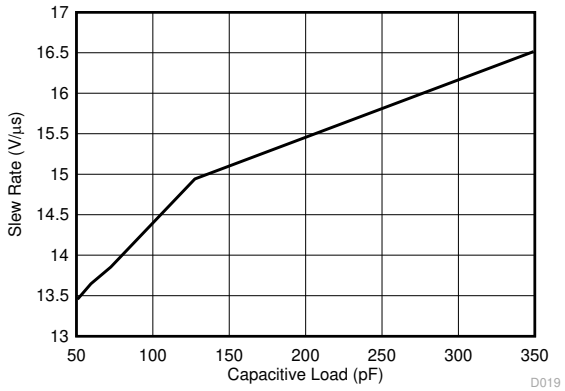
| 部品番号 (1) | チャネル数 | パッケージ | パッケージ サイズ(4) |
|---|---|---|---|
| TLV9051-Q1 | シングル | DBV (SOT-23、5) | 2.90mm × 2.80mm |
| | | DCK (SC70、5)(3) | 2.00mm × 2.10mm |
| TLV9052-Q1 | デュアル | D (SOIC、8)(3) | 4.90mm × 6.00mm |
| | | PW (TSSOP、8) | 3.00mm × 6.40mm |
| | | DGK (VSSOP、8)(3) | 3.00mm × 4.90mm |
| TLV9054-Q1(2) | クワッド | D (SOIC、14)(3) | 8.65mm × 6.00mm |
| | | PW (TSSOP、14)(3) | 5.00mm × 6.40mm |

(1) 詳細については、セクション 10 を参照してください。
(2) このデバイスはプレビュー専用です。
(3) このパッケージはプレビュー専用です。
(4) パッケージ サイズ (長さ×幅) は公称値であり、該当する場合はピンも含まれます。




$$\frac{V_{OUT}}{V_{IN}} = \left(1 + \frac{R_F}{R_G}\right)\left(\frac{1}{1 + sR_1C_1}\right)$$

**シングル ポールのローパス フィルタ**




**スルー レートと負荷容量との関係**

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# 4 Pin Configuration and Functions

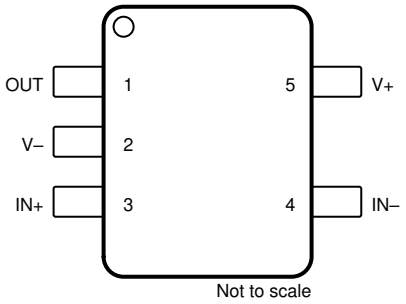



**図 4-1. TLV9051-Q1 DBV Package, 5-Pin SOT-23 (Top View)**

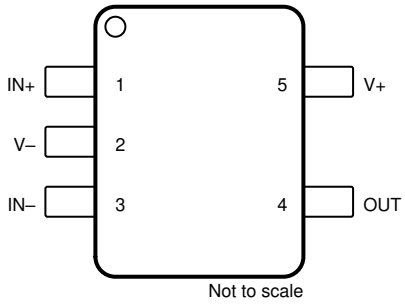



**図 4-2. TLV9051-Q1 DCK Package, 5-Pin SC70 (Top View)**

**表 4-1. Pin Functions: TLV9051-Q1**

| PIN | | | TYPE[1] | DESCRIPTION |
|---|---|---|---|---|
| NAME | SOT-23 | SC-70 | | |
| IN– | 4 | 3 | I | Inverting input |
| IN+ | 3 | 1 | I | Noninverting input |
| OUT | 1 | 4 | O | Output |
| V– | 2 | 2 | — | Negative (low) supply or ground (for single-supply operation) |
| V+ | 5 | 5 | — | Positive (high) supply |

(1) I = input, O = output

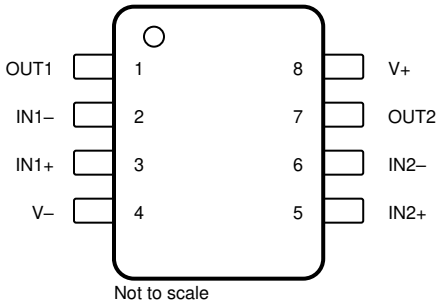



**図 4-3. TLV9052-Q1 D, DGK, PW Packages, 8-Pin SOIC, VSSOP, TSSOP (Top View)**

**表 4-2. Pin Functions: TLV9052-Q1**

| PIN | | TYPE(1) | DESCRIPTION |
|---|---|---|---|
| NAME | NO. | | |
| IN1– | 2 | I | Inverting input, channel 1 |
| IN1+ | 3 | I | Noninverting input, channel 1 |
| IN2– | 6 | I | Inverting input, channel 2 |
| IN2+ | 5 | I | Noninverting input, channel 2 |
| OUT1 | 1 | O | Output, channel 1 |
| OUT2 | 7 | O | Output, channel 2 |
| V– | 4 | — | Negative (low) supply or ground (for single-supply operation) |
| V+ | 8 | — | Positive (high) supply |

(1) I = input, O = output

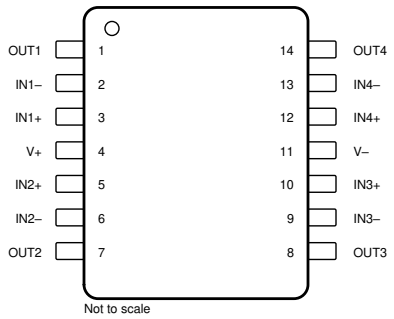



**図 4-4. TLV9054-Q1 D, PW Packages, 14-Pin SOIC, TSSOP (Top View)**

**表 4-3. Pin Functions: TLV9054-Q1**

| PIN | | TYPE(1) | DESCRIPTION |
|---|---|---|---|
| NAME | NO. | | |
| IN1– | 2 | I | Inverting input, channel 1 |
| IN1+ | 3 | I | Noninverting input, channel 1 |
| IN2– | 6 | I | Inverting input, channel 2 |
| IN2+ | 5 | I | Noninverting input, channel 2 |
| IN3– | 9 | I | Inverting input, channel 3 |
| IN3+ | 10 | I | Noninverting input, channel 3 |
| IN4– | 13 | I | Inverting input, channel 4 |
| IN4+ | 12 | I | Noninverting input, channel 4 |
| OUT1 | 1 | O | Output, channel 1 |
| OUT2 | 7 | O | Output, channel 2 |
| OUT3 | 8 | O | Output, channel 3 |
| OUT4 | 14 | O | Output, channel 4 |
| V– | 11 | — | Negative (low) supply or ground (for single-supply operation) |
| V+ | 4 | — | Positive (high) supply |

(1) I = input, O = output

# 5 Specifications

## 5.1 Absolute Maximum Ratings

over operating free-air temperature (unless otherwise noted)(1)

| | | | MIN | MAX | UNIT |
|---|---|---|---|---|---|
| Supply voltage | | | | 7 | V |
| Signal input pins | Voltage(2) | Common-mode | (V–) – 0.5 | (V+) + 0.5 | V |
| | | Differential(4) | | (V+) – (V–) + 0.2 | |
| | Current(2) | | –10 | 10 | mA |
| Output short-circuit(3) | | | Continuous | | mA |
| Temperature | Specified, $T_A$ | | –40 | 125 | °C |
| | Junction, $T_J$ | | | 150 | |
| | Storage, $T_{stg}$ | | –65 | 150 | |

(1) Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute Maximum Ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If used outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.
(2) Input pins are diode-clamped to the power-supply rails. Current limit input signals that can swing more than 0.5V beyond the supply rails to 10mA or less.
(3) Short-circuit to ground, one amplifier per package.
(4) Differential input voltages greater than 0.5 V applied continuously can result in a shift to the input offset voltage and quiescent current above the maximum specifications of these parameters. The magnitude of this effect increases as the ambient operating temperature rises.

## 5.2 ESD Ratings

over operating free-air temperature range (unless otherwise noted)

| | | | VALUE | UNIT |
|---|---|---|---|---|
| $V_{(ESD)}$ - Other Packages | Electrostatic discharge | Human body model (HBM), per AEC-Q100-002(1) | ±4000 | V |
| | | Charged device model (CDM), per AEC-Q100-001 | ±1500 | |

(1) AEC Q100-002 indicates HBM stressing is done in accordance with the ANSI/ESDA/JEDECE JS-001 specification.

## 5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

| | | MIN | MAX | UNIT |
|---|---|---|---|---|
| $V_S$ | Supply voltage | 1.8 | 6 | V |
| $V_I$ | Common mode voltage range | (V–) – 0.1 | (V+) + 0.1 | V |
| $T_A$ | Specified temperature | –40 | 125 | °C |

## 5.4 Thermal Information for Single Channel

| THERMAL METRIC[1] | | TLV9051-Q1 | | UNIT |
|---|---|---|---|---|
| | | DBV (SOT-23) | DCK (SC70) | |
| | | 5 PINS | 5 PINS | |
| $R_{\theta JA}$ | Junction-to-ambient thermal resistance | 232.5 | TBD | °C/W |
| $R_{\theta JC(top)}$ | Junction-to-case (top) thermal resistance | 131.0 | TBD | °C/W |
| $R_{\theta JB}$ | Junction-to-board thermal resistance | 99.6 | TBD | °C/W |
| $\psi_{JT}$ | Junction-to-top characterization parameter | 66.5 | TBD | °C/W |
| $\psi_{JB}$ | Junction-to-board characterization parameter | 99.1 | TBD | °C/W |
| $R_{\theta JC(bot)}$ | Junction-to-case (bottom) thermal resistance | N/A | N/A | °C/W |

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application note.

## 5.5 Thermal Information for Dual Channel

| THERMAL METRIC[1] | | TLV9052-Q1 | | | UNIT |
|---|---|---|---|---|---|
| | | D (SOIC) | DGK (VSSOP) | PW (TSSOP) | |
| | | 8 PINS | 8 PINS | 8 PINS | |
| $R_{\theta JA}$ | Junction-to-ambient thermal resistance | TBD | TBD | 180.5 | °C/W |
| $R_{\theta JC(top)}$ | Junction-to-case (top) thermal resistance | TBD | TBD | 85.2 | °C/W |
| $R_{\theta JB}$ | Junction-to-board thermal resistance | TBD | TBD | 120.7 | °C/W |
| $\psi_{JT}$ | Junction-to-top characterization parameter | TBD | TBD | 15.7 | °C/W |
| $\psi_{JB}$ | Junction-to-board characterization parameter | TBD | TBD | 118.1 | °C/W |
| $R_{\theta JC(bot)}$ | Junction-to-case (bottom) thermal resistance | N/A | N/A | N/A | °C/W |

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application note.

## 5.6 Thermal Information for Quad Channel

| THERMAL METRIC[1] | | TLV9054-Q1 | | UNIT |
|---|---|---|---|---|
| | | D (SOIC) | PW (TSSOP) | |
| | | 14 PINS | 14 PINS | |
| $R_{\theta JA}$ | Junction-to-ambient thermal resistance | TBD | TBD | °C/W |
| $R_{\theta JC(top)}$ | Junction-to-case (top) thermal resistance | TBD | TBD | °C/W |
| $R_{\theta JB}$ | Junction-to-board thermal resistance | TBD | TBD | °C/W |
| $\psi_{JT}$ | Junction-to-top characterization parameter | TBD | TBD | °C/W |
| $\psi_{JB}$ | Junction-to-board characterization parameter | TBD | TBD | °C/W |
| $R_{\theta JC(bot)}$ | Junction-to-case (bottom) thermal resistance | N/A | N/A | °C/W |

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application note.

## 5.7 Electrical Characteristics: $V_S$ (Total Supply Voltage) = (V+) – (V–) = 1.8V to 5.5V

at $T_A$ = 25°C, $R_L$ = 10kΩ connected to $V_S$ / 2, $V_{CM}$ = $V_S$ / 2, and $V_{OUT}$ = $V_S$ / 2 (unless otherwise noted);

| PARAMETER | | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|
| **OFFSET VOLTAGE** | | | | | | |
| $V_{OS}$ | Input offset voltage | $V_S$ = 5V | | ±0.33 | ±1.85 | mV |
| | | $V_S$ = 5V, $T_A$ = –40°C to +125°C | | | ±2.24 | |
| $dV_{OS}/dT$ | Drift | $V_S$ = 5V, $T_A$ = –40°C to +125°C | | ±0.5 | | µV/°C |
| PSRR | Power-supply rejection ratio | $V_S$ = 1.8V – 5.5V, $V_{CM}$ = (V–) | | ±13 | ±80 | µV/V |
| | Channel separation, dc | At dc | | 115 | | dB |
| **INPUT VOLTAGE RANGE** | | | | | | |
| $V_{CM}$ | Common-mode voltage | $V_S$ = 1.8V to 5.5V | (V–) – 0.1 | | (V+) + 0.1 | V |
| CMRR | Common-mode rejection ratio | $V_S$ = 5.5V, (V–) – 0.1V < $V_{CM}$ < (V+) – 1.4V, $T_A$ = –40°C to +125°C | 80 | 96 | | dB |
| | | $V_S$ = 5.5V, $V_{CM}$ = –0.1V to 5.6V, $T_A$ = –40°C to +125°C | 62 | 79 | | |
| | | $V_S$ = 1.8V, (V–) – 0.1V < $V_{CM}$ < (V+) – 1.4V, $T_A$ = –40°C to +125°C | | 88 | | |
| | | $V_S$ = 1.8V, $V_{CM}$ = –0.1V to 1.9V, $T_A$ = –40°C to +125°C | | 72 | | |
| **INPUT BIAS CURRENT** | | | | | | |
| $I_B$ | Input bias current | | | ±2 | ±18[2] | pA |
| | | $T_A$ = –40°C to +125°C | | | ±750[2] | pA |
| $I_{OS}$ | Input offset current | | | ±1 | ±15[2] | pA |
| | | $T_A$ = –40°C to +125°C | | | ±440[2] | pA |
| **NOISE** | | | | | | |
| $E_n$ | Input voltage noise (peak-to-peak) | $V_S$ = 5V, f = 0.1Hz to 10Hz | | 6 | | $µV_{PP}$ |
| $e_n$ | Input voltage noise density | $V_S$ = 5V, f = 10kHz | | 15 | | nV/√Hz |
| | | $V_S$ = 5V, f = 1kHz | | 20 | | nV/√Hz |
| $i_n$ | Input current noise density | f = 1kHz | | 18 | | fA/√Hz |
| **INPUT CAPACITANCE** | | | | | | |
| $C_{ID}$ | Differential | | | 2 | | pF |
| $C_{IC}$ | Common-mode | | | 4 | | pF |
| **OPEN-LOOP GAIN** | | | | | | |
| $A_{OL}$ | Open-loop voltage gain | $V_S$ = 1.8V, (V–) + 0.04V < $V_O$ < (V+) – 0.04V, $R_L$ = 10kΩ | | 106 | | dB |
| | | $V_S$ = 5.5V, (V–) + 0.05V < $V_O$ < (V+) – 0.05V, $R_L$ = 10kΩ | 104 | 128 | | |
| | | $V_S$ = 1.8V, (V–) + 0.06V < $V_O$ < (V+) – 0.06V, $R_L$ = 2kΩ | | 108 | | |
| | | $V_S$ = 5.5V, (V–) + 0.15V < $V_O$ < (V+) – 0.15V, $R_L$ = 2kΩ | | 130 | | |
| **FREQUENCY RESPONSE** | | | | | | |
| GBP | Gain bandwidth product | $V_S$ = 5.5V, G = +1 | | 5 | | MHz |
| $φ_m$ | Phase margin | $V_S$ = 5.5V, G = +1 | | 60 | | Degrees |
| SR | Slew rate | $V_S$ = 5.5V, G = +1, $C_L$ = 130pF | | 15 | | V/µs |
| $t_S$ | Settling time | To 0.1%, $V_S$ = 5.5V, 2V step , G = +1, $C_L$ = 100pF | | 0.75 | | µs |
| | | To 0.01%, $V_S$ = 5.5V, 2V step , G = +1, $C_L$ = 100pF | | 1 | | |
| $t_{OR}$ | Overload recovery time | $V_S$ = 5.5V, $V_{IN}$ × gain > $V_S$ | | 0.3 | | µs |
| THD + N | Total harmonic distortion + noise[1] | $V_S$ = 5.5V, $V_{CM}$ = 2.5V, $V_O$ = 1$V_{RMS}$, G = +1, f = 1kHz | | 0.0006% | | |
| **OUTPUT** | | | | | | |

## 5.7 Electrical Characteristics: $V_S$ (Total Supply Voltage) = (V+) – (V–) = 1.8V to 5.5V (続き)

at $T_A$ = 25°C, $R_L$ = 10kΩ connected to $V_S$ / 2, $V_{CM}$ = $V_S$ / 2, and $V_{OUT}$ = $V_S$ / 2 (unless otherwise noted);

| PARAMETER | | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|
| $V_O$ | Voltage output swing from supply rails | $V_S$ = 5.5V, $R_L$ = 10kΩ, | | | 16 | mV |
| | | $V_S$ = 5.5V, $R_L$ = 2kΩ, | | | 40 | |
| $I_{SC}$ | Short-circuit current | $V_S$ = 5V | | ±50 | | mA |
| $Z_O$ | Open-loop output impedance | $V_S$ = 5V, f = 5MHz | | 250 | | Ω |
| **POWER SUPPLY** | | | | | | |
| $I_Q$ | Quiescent current per amplifier | $V_S$ = 5.5V, $I_O$ = 0mA, | | 330 | 450 | µA |
| | | $V_S$ = 5.5V, $I_O$ = 0mA, $T_A$ = –40°C to +125°C | | | 475 | |

(1) Third-order filter; bandwidth = 80kHz at –3dB.
(2) Specified by design and characterization; not production tested.

## 5.8 Typical Characteristics

at $T_A$ = 25°C, $V_S$ = 5.5V, $R_L$ = 10kΩ connected to $V_S$ / 2, $V_{CM}$ = $V_S$ / 2, and $V_{OUT}$ = $V_S$ / 2 (unless otherwise noted)

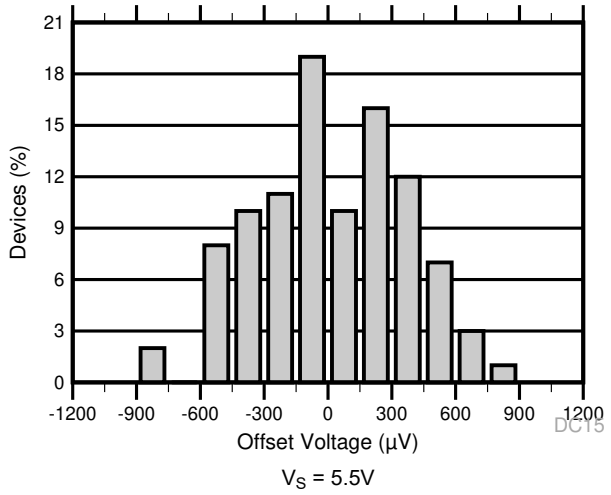



図 5-1. Offset Voltage Production Distribution

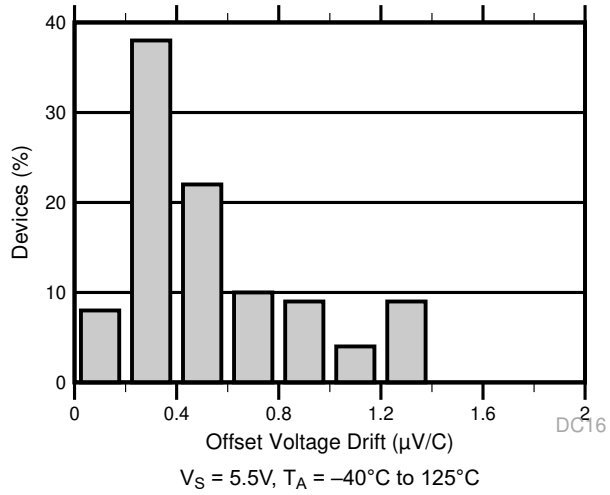



図 5-2. Offset Voltage Drift Distribution

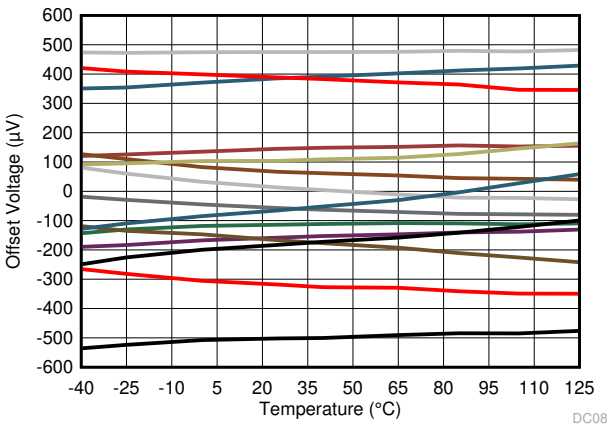



図 5-3. Offset Voltage vs Temperature

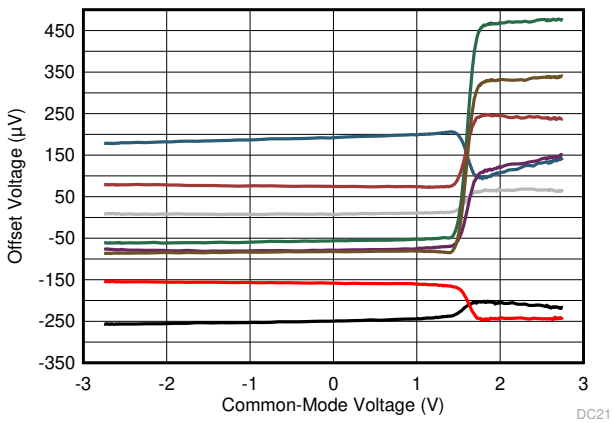



図 5-4. Offset Voltage vs Common-Mode Voltage

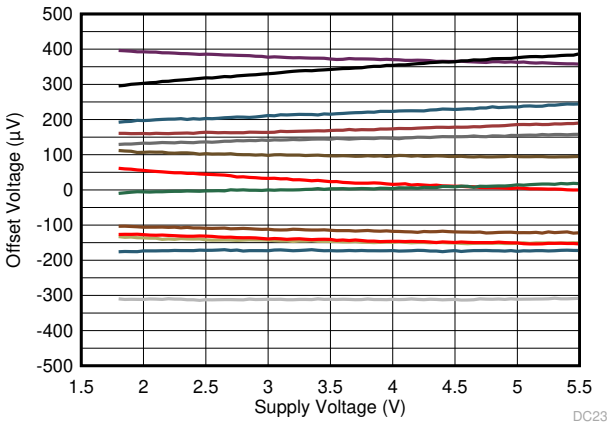



図 5-5. Offset Voltage vs Power Supply

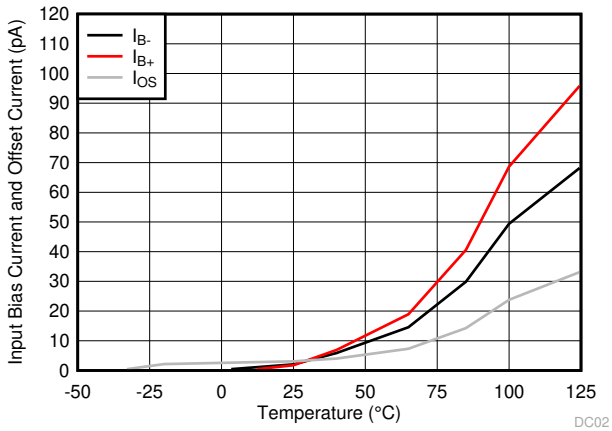



図 5-6. Input Bias Current vs Temperature

## 5.8 Typical Characteristics (continued)

at $T_A$ = 25°C, $V_S$ = 5.5V, $R_L$ = 10kΩ connected to $V_S$ / 2, $V_{CM}$ = $V_S$ / 2, and $V_{OUT}$ = $V_S$ / 2 (unless otherwise noted)

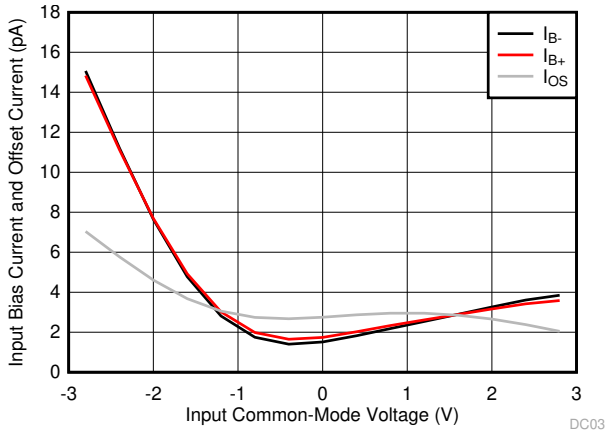



図 5-7. Input Bias Current and Offset Current vs Common-Mode Voltage

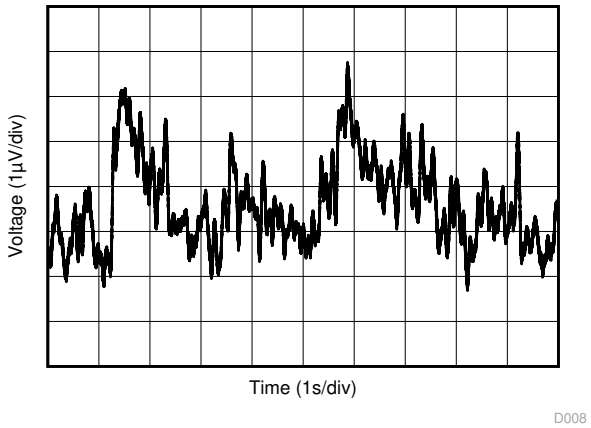



図 5-8. 0.1Hz to 10Hz Input Voltage Noise

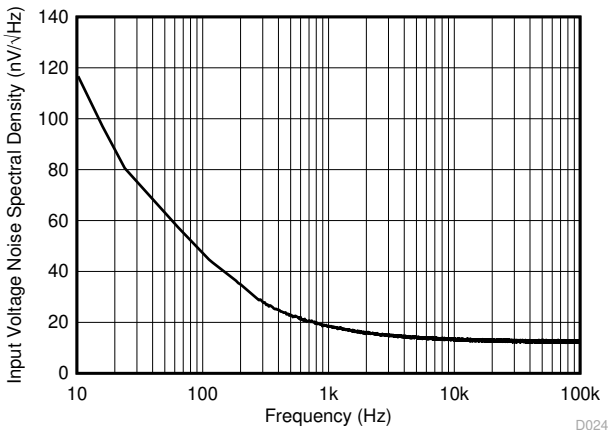



図 5-9. Input Voltage Noise Spectral Density vs Frequency

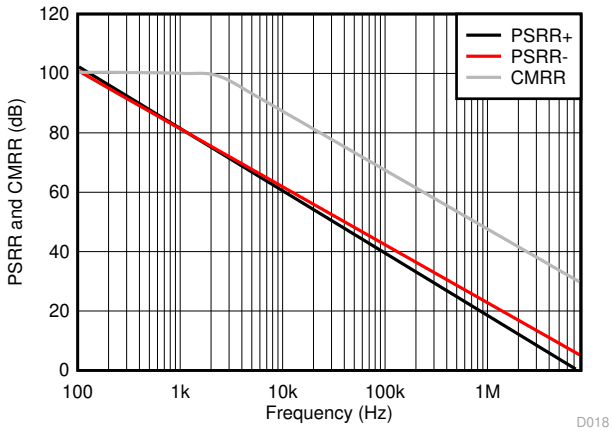



図 5-10. CMRR and PSRR vs Frequency (Referred to Input)

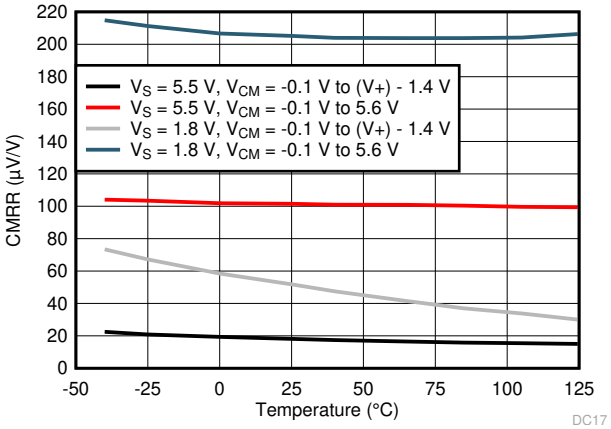



図 5-11. CMRR vs Temperature

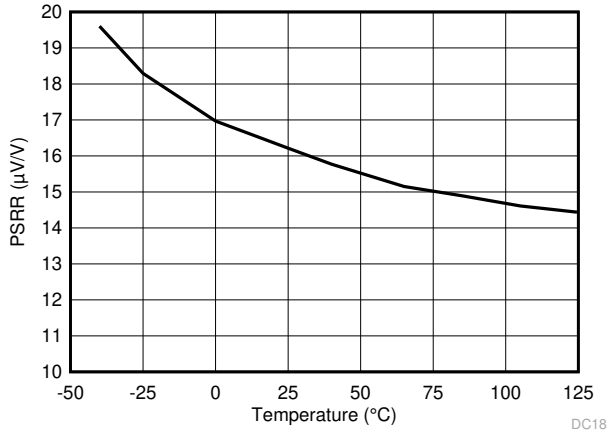



図 5-12. PSRR vs Temperature

## 5.8 Typical Characteristics (continued)

at $T_A$ = 25°C, $V_S$ = 5.5V, $R_L$ = 10kΩ connected to $V_S$ / 2, $V_{CM}$ = $V_S$ / 2, and $V_{OUT}$ = $V_S$ / 2 (unless otherwise noted)

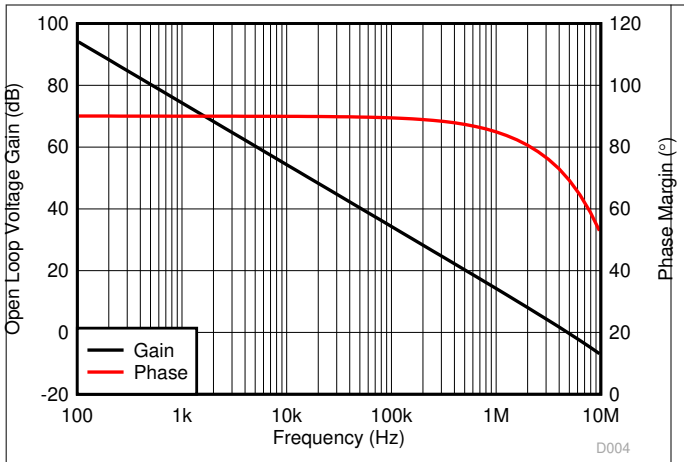



図 5-13. Open Loop Voltage Gain and Phase vs Frequency

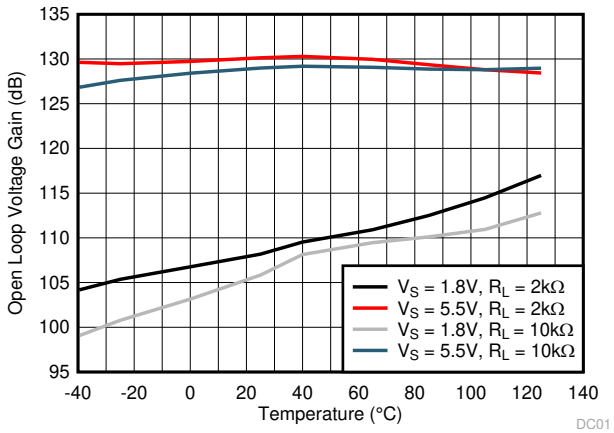



図 5-14. Open Loop Voltage Gain vs Temperature

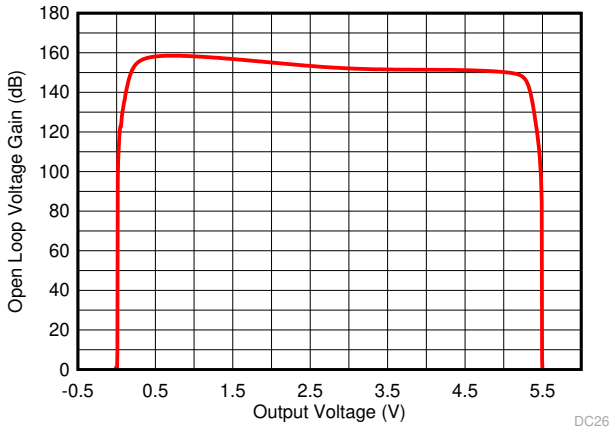



図 5-15. Open Loop Voltage Gain vs Output Voltage

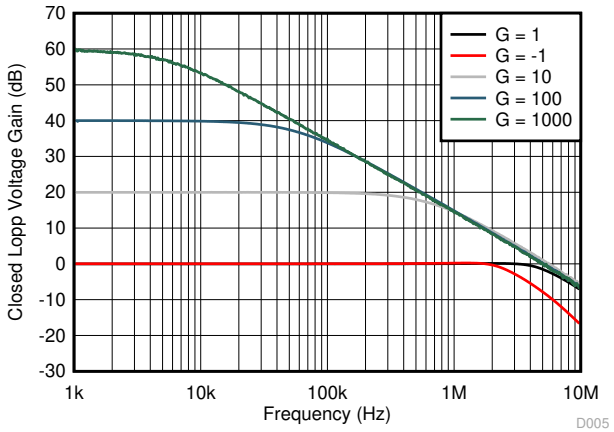



図 5-16. Closed Loop Voltage Gain vs Frequency

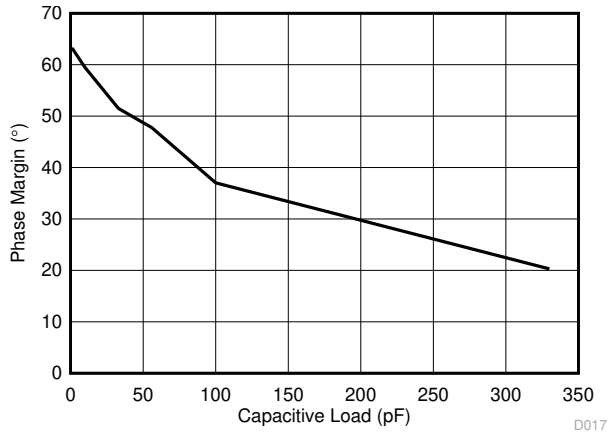



図 5-17. Phase Margin vs Capacitive Load

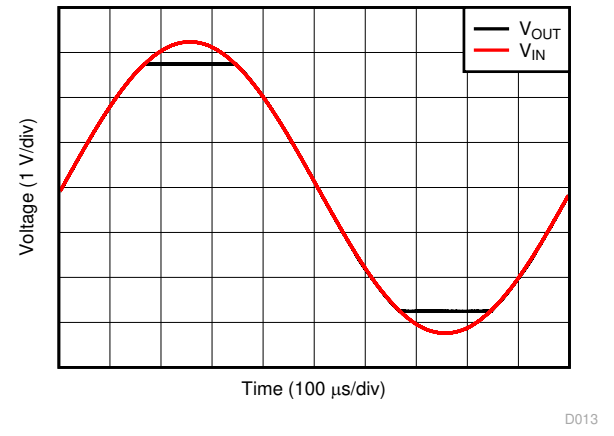
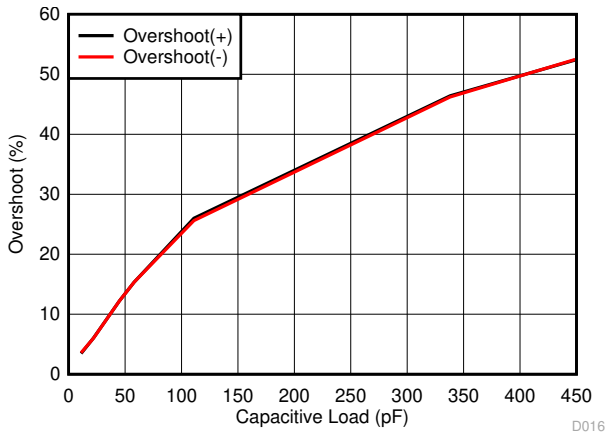



図 5-18. No Phase Reversal

## 5.8 Typical Characteristics (continued)

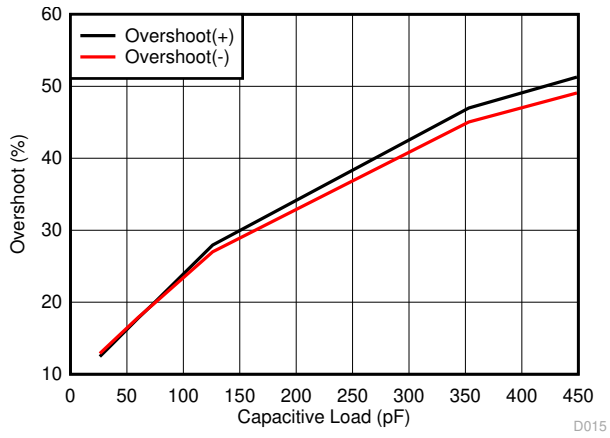
at $T_A$ = 25°C, $V_S$ = 5.5V, $R_L$ = 10kΩ connected to $V_S$ / 2, $V_{CM}$ = $V_S$ / 2, and $V_{OUT}$ = $V_S$ / 2 (unless otherwise noted)




G = +1V/V

$V_{OUT}$ step = 100$mV_{p-p}$

**図 5-19. Small-Signal Overshoot vs Load Capacitance**




G = –1V/V

$V_{OUT}$ step = 100$mV_{p-p}$

**図 5-20. Small-Signal Overshoot vs Load Capacitance**

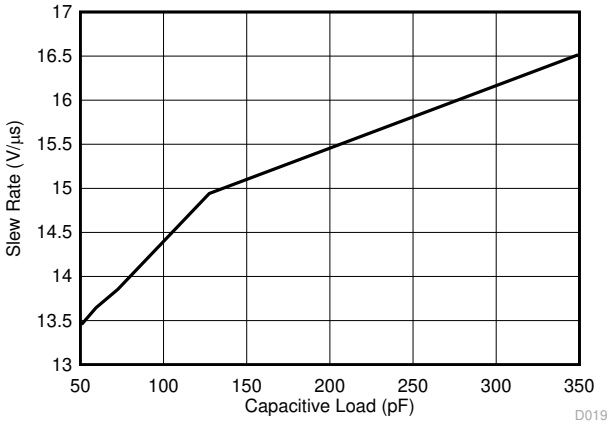
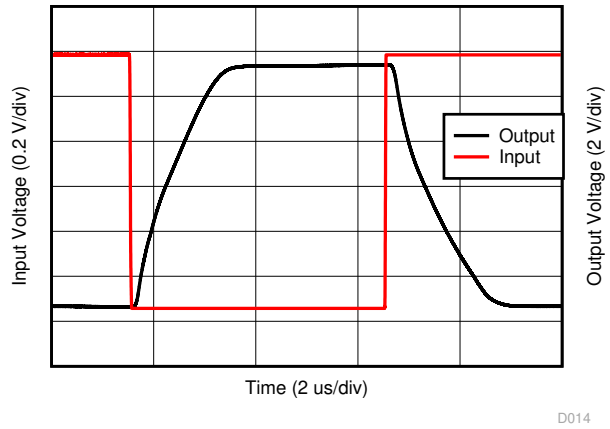
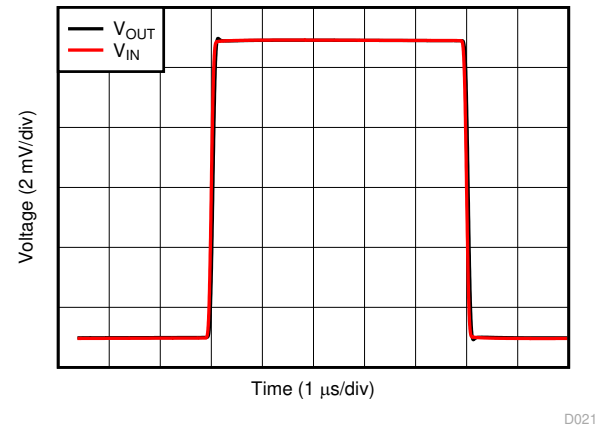



**図 5-21. Slew Rate vs Capacitive Load**




G = –10V/V

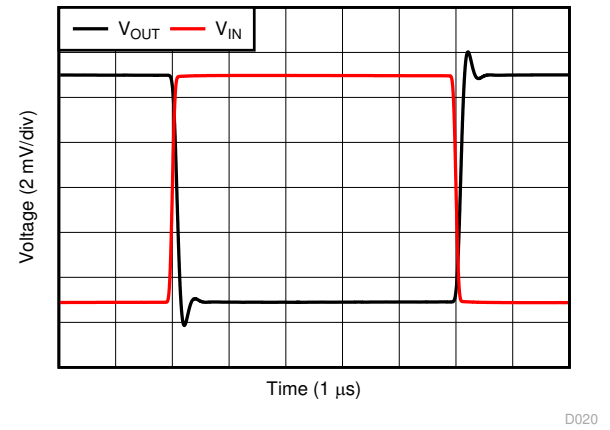
**図 5-22. Overload Recovery**




G = +1V/V

$V_{OUT}$ step = 10$mV_{p-p}$

**図 5-23. Small-Signal Step Response**



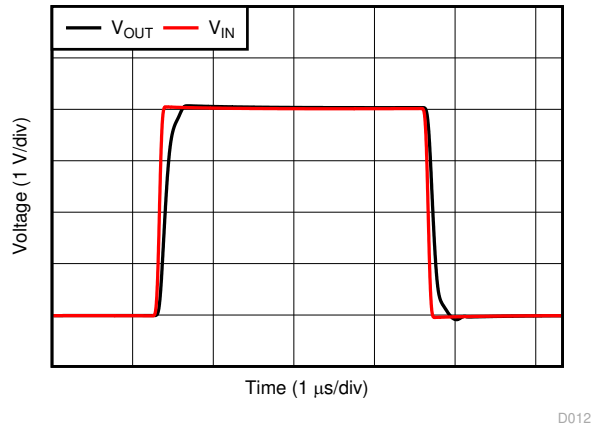

G = –1V/V

$V_{OUT}$ step = 10$mV_{p-p}$

**図 5-24. Small-Signal Step Response**

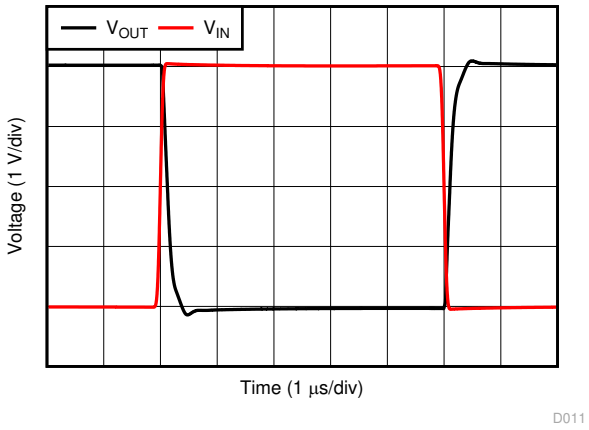
## 5.8 Typical Characteristics (continued)

at $T_A$ = 25°C, $V_S$ = 5.5V, $R_L$ = 10kΩ connected to $V_S$ / 2, $V_{CM}$ = $V_S$ / 2, and $V_{OUT}$ = $V_S$ / 2 (unless otherwise noted)



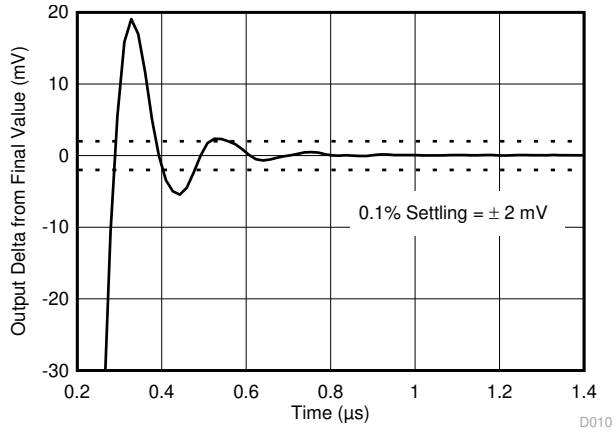

G = +1V/V
$V_{OUT}$ step = $4V_{p-p}$

**図 5-25. Large-Signal Step Response**



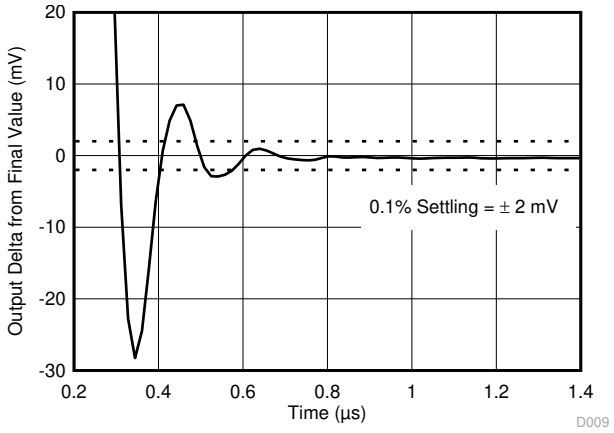

G = –1V/V
$V_{OUT}$ step = $4V_{p-p}$

**図 5-26. Large-Signal Step Response**



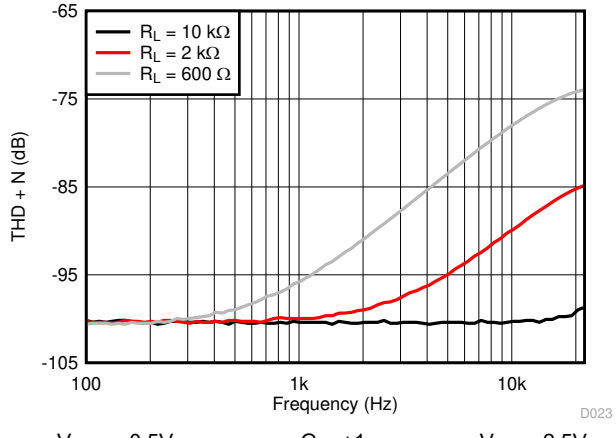

$C_L$ = 100pF G = +1V/V

**図 5-27. Positive Large-Signal Settling Time**



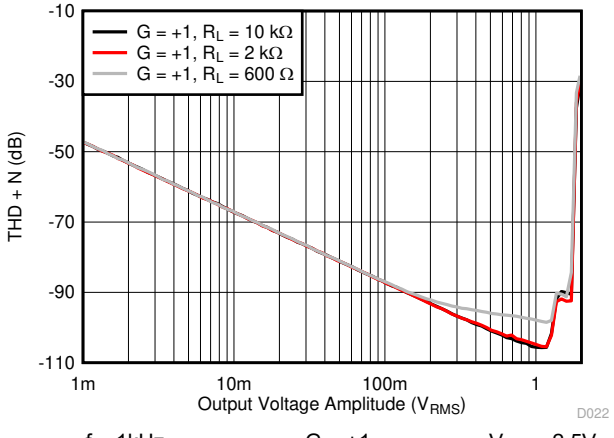

$C_L$ = 100pF G = +1V/V

**図 5-28. Negative Large-Signal Settling Time**




$V_{OUT}$ = 0.5$V_{RMS}$ G = +1 $V_{CM}$ = 2.5V
BW = 80kHz

**図 5-29. THD + N vs Frequency**




f = 1kHz G = +1 $V_{CM}$ = 2.5V
BW = 80kHz

**図 5-30. THD + N vs Amplitude**

## 5.8 Typical Characteristics (continued)

at $T_A$ = 25°C, $V_S$ = 5.5V, $R_L$ = 10kΩ connected to $V_S$ / 2, $V_{CM}$ = $V_S$ / 2, and $V_{OUT}$ = $V_S$ / 2 (unless otherwise noted)

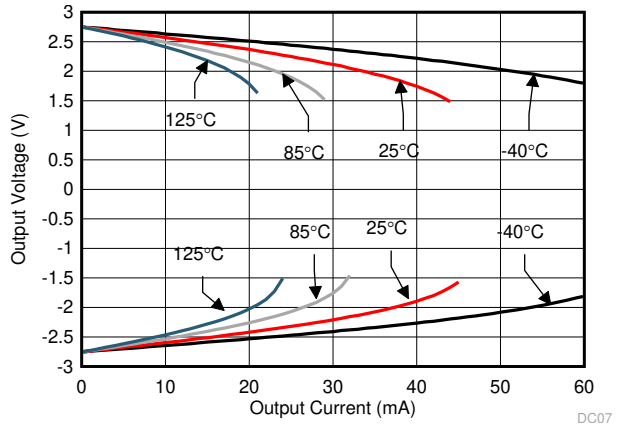



図 5-31. Output Voltage Swing vs Output Current

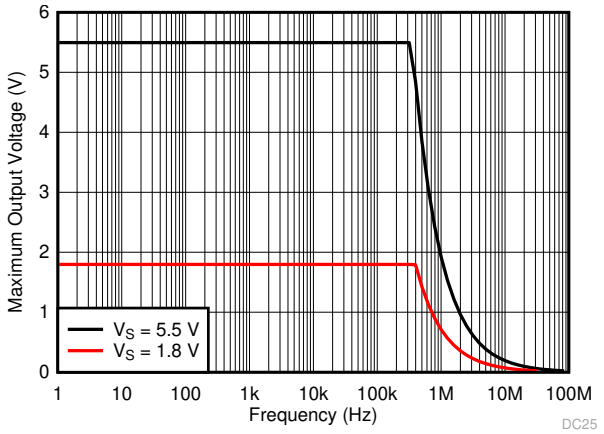



図 5-32. Maximum Output Voltage vs Frequency and Supply Voltage

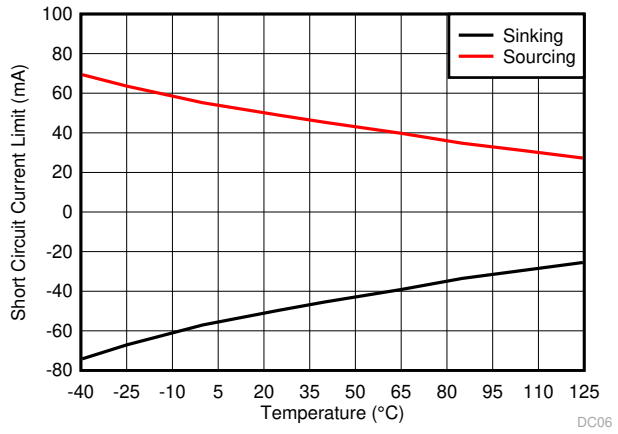



図 5-33. Short-Circuit Current vs Temperature

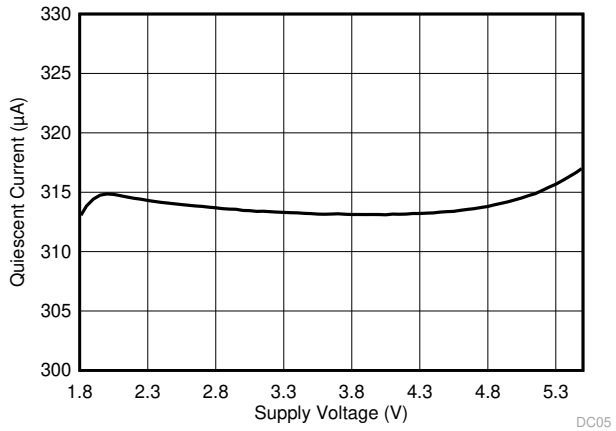



図 5-34. Quiescent Current vs Supply Voltage

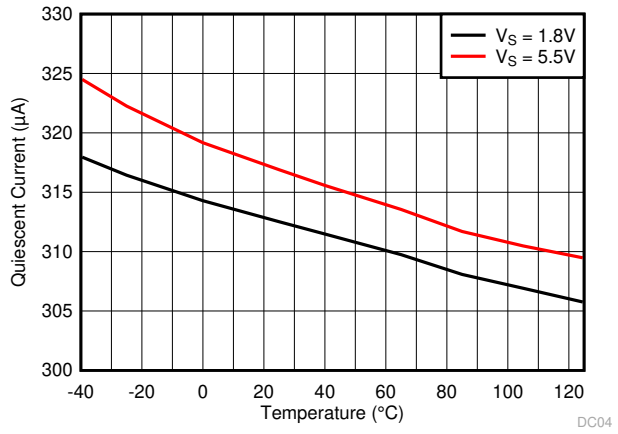



図 5-35. Quiescent Current vs Temperature

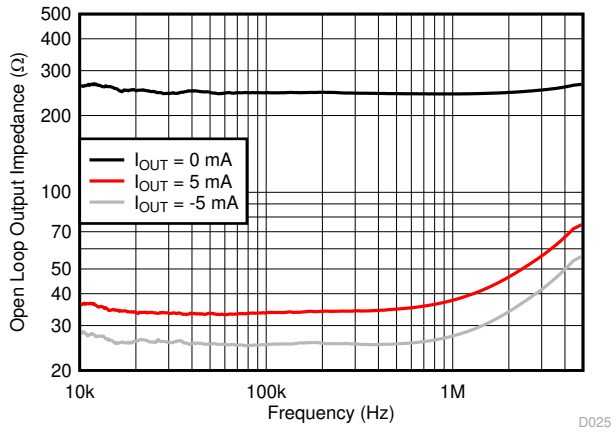
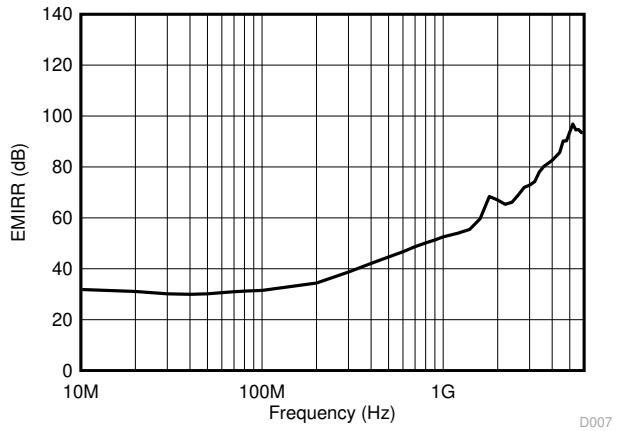



図 5-36. Open-Loop Output Impedance vs Frequency

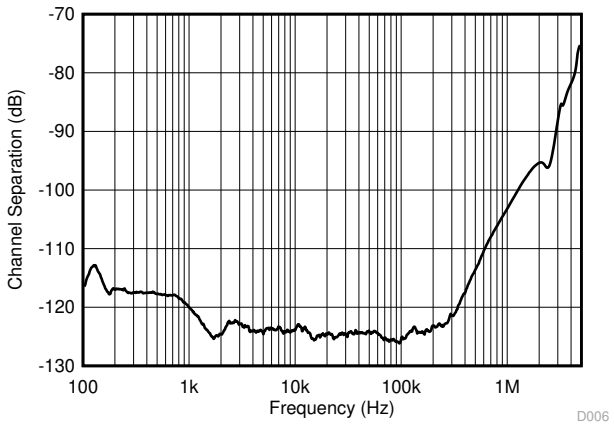
## 5.8 Typical Characteristics (continued)

at $T_A$ = 25°C, $V_S$ = 5.5V, $R_L$ = 10kΩ connected to $V_S$ / 2, $V_{CM}$ = $V_S$ / 2, and $V_{OUT}$ = $V_S$ / 2 (unless otherwise noted)




$P_{RF}$ = –10dBm

**図 5-37. Electromagnetic Interference Rejection Ratio Referred to Noninverting Input (EMIRR+) vs Frequency**




$P_{RF}$ = –10dBm

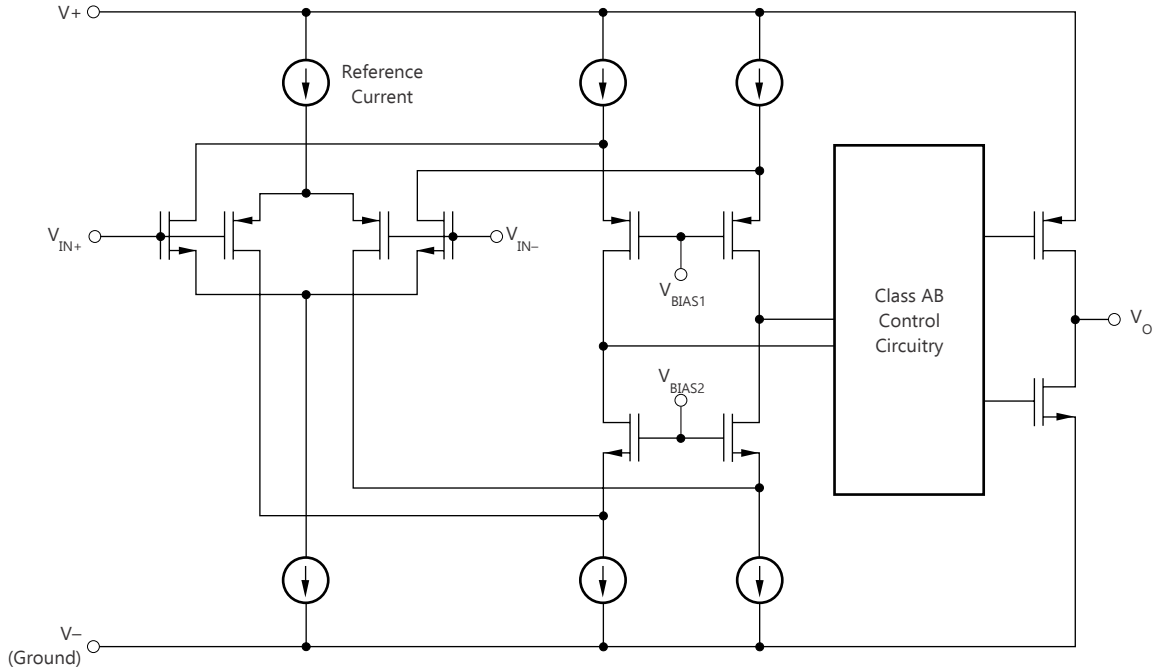
**図 5-38. Channel Separation vs Frequency**

# 6 Detailed Description

## 6.1 Overview

The TLV905x-Q1 devices are a 5MHz family of low-power, rail-to-rail input and output op amps. These devices operate from 1.8V to 6V, are unity-gain stable, and are designed for a wide range of general-purpose applications. The input common-mode voltage range includes both rails and allows the TLV905x-Q1 family to be used in virtually any single-supply application. The unique combination of a high slew rate and low quiescent current makes this family a potential choice for battery-powered motor-drive applications. Rail-to-rail input and output swing significantly increases dynamic range, especially in low-supply applications.

## 6.2 Functional Block Diagram



## 6.3 Feature Description

### 6.3.1 Operating Voltage

The TLV905x-Q1 family of op amps is specified for operation from 1.8V to 6.0V. In addition, many specifications apply from –40°C to 125°C. Parameters that vary significantly with operating voltages or temperature are illustrated in the *Typical Characteristics*.

### 6.3.2 Rail-to-Rail Input

The input common-mode voltage range of the TLV905x-Q1 family extends 100mV beyond the supply rails for the full supply voltage range of 1.8V to 6.0V. This performance is achieved with a complementary input stage: an N-channel input differential pair in parallel with a P-channel differential pair, as shown in the *Functional Block Diagram*. The N-channel pair is active for input voltages close to the positive rail, typically (V+) – 1.4V to 200mV above the positive supply, whereas the P-channel pair is active for inputs from 200mV below the negative supply to approximately (V+) – 1.4V. There is a small transition region, typically (V+) – 1.2V to (V+) – 1V, in which both pairs are on. This 200mV transition region can vary up to 200mV with process variation. Thus, the transition region (with both stages on) can range from (V+) – 1.4V to (V+) – 1.2V on the low end, and up to (V+) – 1V to (V+) – 0.8V on the high end. Within this transition region, PSRR, CMRR, offset voltage, offset drift, and THD can degrade compared to device operation outside this region.

### 6.3.3 Rail-to-Rail Output

Designed as low-power, low-voltage operational amplifiers, the TLV905x-Q1 family delivers a robust output drive capability. A class AB output stage with common-source transistors achieves full rail-to-rail output swing capability. For resistive loads of 10kΩ, the output swings to within 16mV of either supply rail, regardless of the applied power-supply voltage. Different load conditions change the ability of the amplifier to swing close to the rails.

### 6.3.4 EMI Rejection

The TLV905x-Q1 uses integrated electromagnetic interference (EMI) filtering to reduce the effects of EMI from sources such as wireless communications and densely-populated boards with a mix of analog signal chain and digital components. EMI immunity can be improved with circuit design techniques; the TLV905x-Q1 benefits from these design improvements. Texas Instruments has developed the ability to accurately measure and quantify the immunity of an operational amplifier over a broad frequency spectrum extending from 10MHz to 6GHz. 図 6-1 shows the results of this testing on the TLV905x-Q1. 表 6-1 lists the EMIRR IN+ values for the TLV905x-Q1 at particular frequencies commonly encountered in real-world applications. The *EMI Rejection Ratio of Operational Amplifiers* application note contains detailed information on the topic of EMIRR performance as it relates to operational amplifiers.

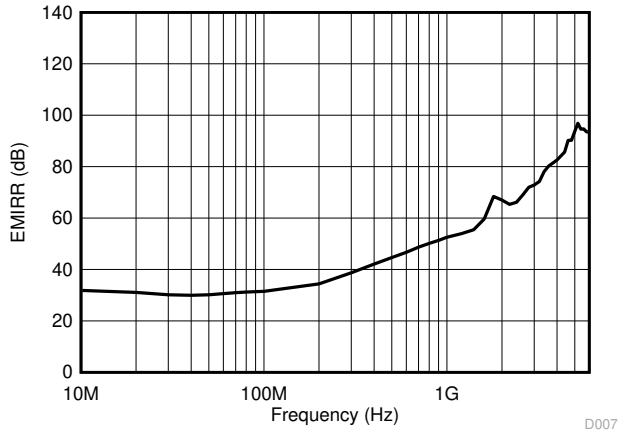



**図 6-1. EMIRR Testing**

**表 6-1. TLV905x-Q1 EMIRR IN+ for Frequencies of Interest**

| FREQUENCY | APPLICATION OR ALLOCATION | EMIRR IN+ |
|---|---|---|
| 400MHz | Mobile radio, mobile satellite, space operation, weather, radar, ultra-high frequency (UHF) applications | 41.8dB |
| 900MHz | Global system for mobile communications (GSM) applications, radio communication, navigation, GPS (to 1.6GHz), GSM, aeronautical mobile, UHF applications | 53.1dB |
| 1.8GHz | GSM applications, mobile personal communications, broadband, satellite, L-band (1GHz to 2GHz) | 71.8dB |
| 2.4GHz | 802.11b, 802.11g, 802.11n, Bluetooth®, mobile personal communications, industrial, scientific and medical (ISM) radio band, amateur radio and satellite, S-band (2GHz to 4GHz) | 70.0dB |
| 3.6GHz | Radiolocation, aero communication and navigation, satellite, mobile, S-band | 81.2dB |
| 5GHz | 802.11a, 802.11n, aero communication and navigation, mobile communication, space and satellite operation, C-band (4GHz to 8GHz) | 92.5dB |

### *6.3.5 Overload Recovery*

Overload recovery is defined as the time required for the operational amplifier output to recover from a saturated state to a linear state. The output devices of the operational amplifier enter a saturation region when the output voltage exceeds the rated operating voltage, because of the high input voltage or high gain. After the device enters the saturation region, the output devices require time to return to the linear operating state. After the output devices return to a linear operating state, the device begins to slew at the specified slew rate. Therefore, the propagation delay (in case of an overload condition) is the sum of the overload recovery time and the slew time. The overload recovery time for the TLV905x-Q1 family is approximately 300ns.

### *6.3.6 Electrical Overstress*

Designers often ask questions about the capability of an operational amplifier to withstand electrical overstress. These questions tend to focus on the device inputs, but can involve the supply voltage pins or even the output pin. Each of these different pin functions have electrical stress limits determined by the voltage breakdown characteristics of the particular semiconductor fabrication process and specific circuits connected to the pin. Additionally, internal electrostatic discharge (ESD) protection is built into these circuits to protect them from accidental ESD events both before and during product assembly.

Having a good understanding of this basic ESD circuitry and the relevance ESD circuitry has to an electrical overstress event is helpful. 図 6-2 shows the ESD circuits contained in the TLV905x-Q1 devices. The ESD protection circuitry involves several current-steering diodes connected from the input and output pins and routed back to the internal power supply lines, where the diode routes meet at an absorption device internal to the operational amplifier. This protection circuitry is intended to remain inactive during normal circuit operation.

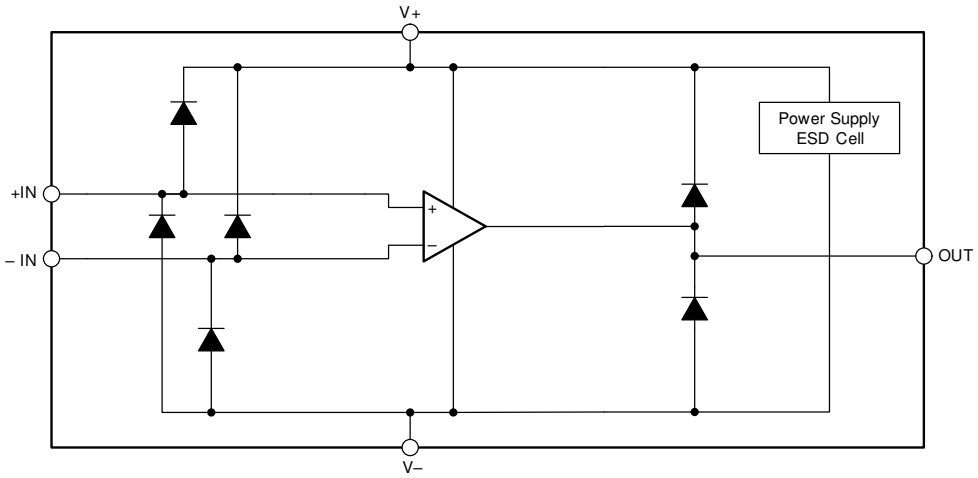



**図 6-2. Equivalent Internal ESD Circuitry**

### 6.3.7 Input Protection

The TLV905x-Q1 family incorporates internal ESD protection circuits on all pins. For input and output pins, this protection primarily consists of current-steering diodes connected between the input and power-supply pins. These ESD protection diodes provide in-circuit, input overdrive protection, as long as the current is limited to 10mA (for more information, see *Absolute Maximum Ratings*). 図 6-3 shows how a series input resistor can be added to the driven input to limit the input current. The added resistor contributes thermal noise at the amplifier input and the value must be kept to a minimum in noise-sensitive applications.

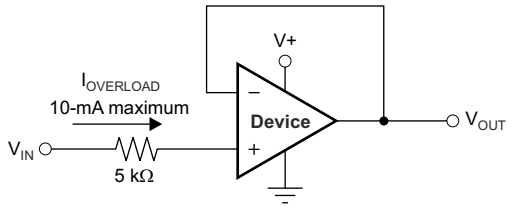



**図 6-3. Input Current Protection**

## 6.4 Device Functional Modes

The TLV905x-Q1 family is operational when the power-supply voltage is between 1.8V (±0.9V) and 6.0V (±3.0V).

# 7 Application and Implementation

注

以下のアプリケーションに関するセクションの情報は、TI の部品仕様の一部ではなく、TI はこれらの情報の正確性や完全性を保証しません。個々の目的に対する製品の適合性については、お客様の責任で判断していただくことになります。また、お客様は自身の設計実装を検証しテストすることで、システムの機能を確認する必要があります。

## 7.1 Application Information

The TLV905x-Q1 family features 5MHz bandwidth and very high slew rate of 15V/µs with only 330µA of supply current per channel, providing excellent AC performance at very low-power consumption. DC applications are well served with a very low input noise voltage of 15nV/√Hz at 10kHz, low input bias current, and a typical input offset voltage of 0.33mV.

## 7.2 Typical Low-Side Current Sense Application

図 7-1 shows the TLV905x-Q1 configured in a low-side current sensing application.

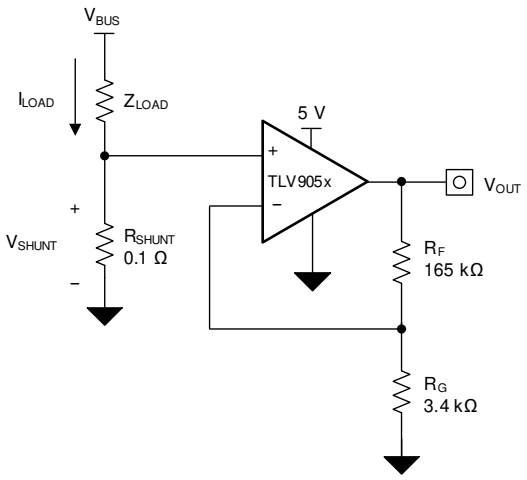



**図 7-1. TLV905x-Q1 in a Low-Side, Current-Sensing Application**

### *7.2.1 Design Requirements*

The design requirements for this design are:

- Load current: 0A to 1A
- Output voltage: 4.95V
- Maximum shunt voltage: 100mV

### 7.2.2 Detailed Design Procedure

The transfer function of the circuit in 図 7-1 is given in 式 1.

$$V_{OUT} = I_{LOAD} \times R_{SHUNT} \times Gain \quad (1)$$

The load current ($I_{LOAD}$) produces a voltage drop across the shunt resistor ($R_{SHUNT}$). The load current is set from 0A to 1A. To keep the shunt voltage below 100mV at maximum load current, the largest shunt resistor is defined using 式 2.

$$R_{SHUNT} = \frac{V_{SHUNT\_MAX}}{I_{LOAD\_MAX}} = \frac{100\ mV}{1\ A} = 100\ m\Omega \quad (2)$$

Using 式 2, $R_{SHUNT}$ equals 100mΩ. The voltage drop produced by $I_{LOAD}$ and $R_{SHUNT}$ is amplified by the TLV905x-Q1 device to produce an output voltage of approximately 0V to 4.95V. 式 3 calculates the gain required for the TLV905x-Q1 device to produce the required output voltage.

$$Gain = \frac{(V_{OUT\_MAX} - V_{OUT_{MIN}})}{(V_{IN\_MAX} - V_{IN\_MIN})} \quad (3)$$

Using 式 3, the required gain equals 49.5V/V, which is set with the $R_F$ and $R_G$ resistors. 式 4 sizes the $R_F$ and $R_G$, resistors to set the gain of the TLV905x-Q1 device to 49.5V/V.

$$Gain = 1 + \frac{(R_F)}{(R_G)} \quad (4)$$

Selecting $R_F$ to equal 165kΩ and $R_G$ to equal 3.4kΩ provides a combination that equals approximately 49.5V/V. 図 7-2 shows the measured transfer function of the circuit shown in 図 7-1.

### 7.2.3 Application Curve

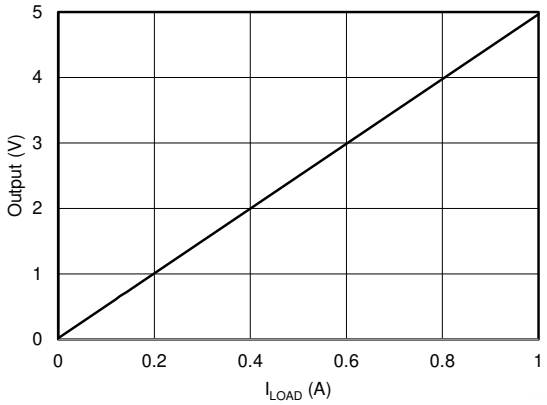



**図 7-2. Low-Side, Current-Sense Transfer Function**

## 7.3 Power Supply Recommendations

The TLV905x-Q1 family is specified for operation from 1.8V to 6.0V (±0.9V to ±3.0V); many specifications apply from –40°C to 125°C. The *Typical Characteristics* section presents parameters that can exhibit significant variance with regard to operating voltage or temperature.

> **注意**
>
> Supply voltages larger than 7V can permanently damage the device; for more information, see the *Absolute Maximum Ratings* table.

Place 0.1µF bypass capacitors close to the power-supply pins to reduce errors coupling in from noisy or high-impedance power supplies. For more-detailed information on bypass capacitor placement, see 図 7-3.

## 7.4 Layout

### 7.4.1 Layout Guidelines

For best operational performance of the device, use good printed circuit board (PCB) layout practices, including:

- Noise can propagate into analog circuitry through the power pins of the circuit as a whole, as well as through the op amp. Bypass capacitors are used to reduce the coupled noise by providing low-impedance power sources local to the analog circuitry.
  - Connect low-ESR, 0.1µF ceramic bypass capacitors between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from V+ to ground is applicable for single-supply applications.
- Separate grounding for analog and digital portions of circuitry is one of the simplest and most-effective methods of noise suppression. One or more layers on multilayer PCBs are usually devoted to ground planes. A ground plane helps distribute heat and reduces electromagnetic interference (EMI) noise pickup. Take care to physically separate digital and analog grounds, paying attention to the flow of the ground current. For more detailed information, see *Circuit Board Layout Techniques*.
- To reduce parasitic coupling, run the input traces as far away from the supply or output traces as possible. If these traces cannot be kept separate, crossing the sensitive trace perpendicular is much better as opposed to in parallel with the noisy trace.
- Place the external components as close to the device as possible. As illustrated in 図 7-3, keeping $R_F$ and $R_G$ close to the inverting input minimizes parasitic capacitance on the inverting input.
- Keep the length of input traces as short as possible. Always remember that the input traces are the most sensitive part of the circuit.
- Consider a driven, low-impedance guard ring around the critical traces. A guard ring can significantly reduce leakage currents from nearby traces that are at different potentials.
- Cleaning the PCB following board assembly is recommended for best performance.
- Any precision integrated circuit can experience performance shifts resulting from moisture ingress into the plastic package. Following any aqueous PCB cleaning process, baking the PCB assembly is recommended to remove moisture introduced into the device packaging during the cleaning process. A low-temperature, post-cleaning bake at 85°C for 30 minutes is sufficient for most circumstances.

### 7.4.2 Layout Example

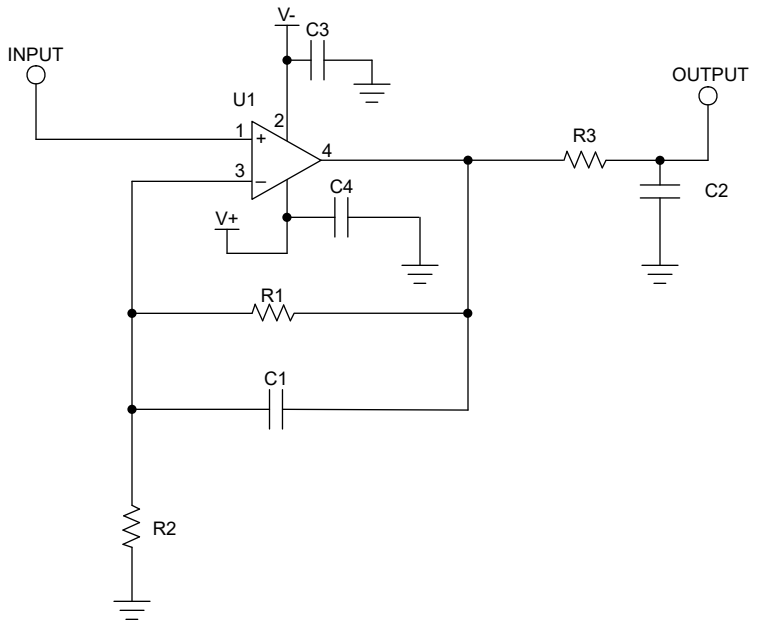



**図 7-3. Schematic for Noninverting Configuration Layout Example**

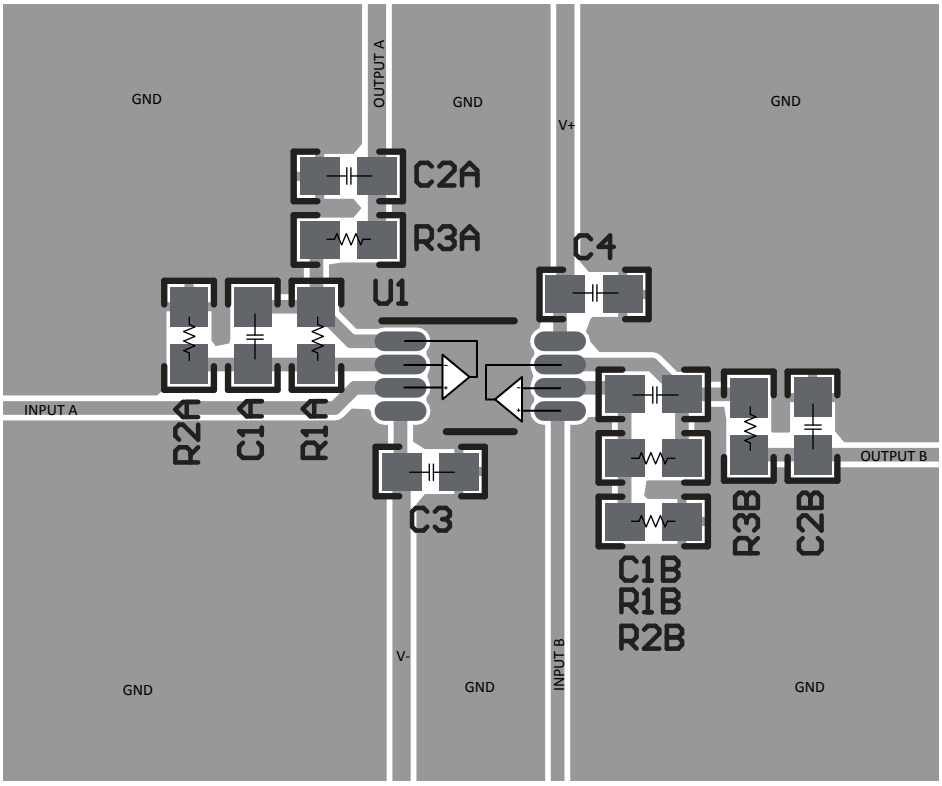



**図 7-4. Example Layout for VSSOP-8 (DGK) Package**

# 8 Device and Documentation Support

## 8.1 Device Support

### *8.1.1 Development Support*

#### 8.1.1.1 TINA-TI™ (Free Software Download)

TINA™ is a simple, powerful, and easy-to-use circuit simulation program based on a SPICE engine. TINA-TI is a free, fully-functional version of the TINA software, preloaded with a library of macro models in addition to a range of both passive and active models. TINA-TI provides all the conventional dc, transient, and frequency domain analysis of SPICE, as well as additional design capabilities.

Available as a free download from the Analog eLab Design Center, TINA-TI offers extensive post-processing capability that allows users to format results in a variety of ways. Virtual instruments offer the ability to select input waveforms and probe circuit nodes, voltages, and waveforms, creating a dynamic quick-start tool.

注

These files require that either the TINA software (from DesignSoft™) or TINA-TI software be installed. Download the free TINA-TI software from the TINA-TI folder.

## 8.2 Documentation Support

### *8.2.1 Related Documentation*

For related documentation, see the following:

- Texas Instruments, *EMI Rejection Ratio of Operational Amplifiers* application note
- Texas Instruments, *Low Voltage, High Slew Rate Op-amps for Motor Drive Circuits* application note
- Texas Instruments, *TI Analog Circuit Cookbook* Analog Engineer's Circuit
- Texas Instruments, *TI Precision Labs - Amplifiers* training video

## 8.3 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、www.tij.co.jp のデバイス製品フォルダを開いてください。[通知] をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取ることができます。 変更の詳細については、改訂されたドキュメントに含まれている改訂履歴をご覧ください。

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### 8.7 用語集

テキサス・インスツルメンツ用語集　この用語集には、用語や略語の一覧および定義が記載されています。

## 9 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

| Changes from Revision A (May 2024) to Revision B (May 2024) | Page |
|---|---|
| • Added footnote about extended high differential input voltage usage | 6 |
| • Changed the maximum input offset voltage across temperature from 2mV to 2.24mV | 8 |

| Changes from Revision * (February 2024) to Revision A (May 2024) | Page |
|---|---|
| • 「特長」セクションに AEC-Q100 認定内容を追加 | 1 |
| • SOT-23 (5) および TSSOP (8) パッケージのステータスをプレビューからアクティブに変更 | 1 |

## 10 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most-current data available for the designated devices. This data is subject to change without notice and without revision of this document. For browser-based versions of this data sheet, see the left-hand navigation pane.

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## PACKAGING INFORMATION

| Orderable Device | Status (1) | Package Type | Package Drawing | Pins | Package Qty | Eco Plan (2) | Lead finish/ Ball material (6) | MSL Peak Temp (3) | Op Temp (°C) | Device Marking (4/5) | Samples |
|---|---|---|---|---|---|---|---|---|---|---|---|
| TLV9051QDBVRQ1 | ACTIVE | SOT-23 | DBV | 5 | 3000 | RoHS & Green | Call TI | Level-1-260C-UNLIM | -40 to 125 | TL51Q | Samples |
| TLV9052QPWRQ1 | ACTIVE | TSSOP | PW | 8 | 3000 | RoHS & Green | NIPDAU | Level-1-260C-UNLIM | -40 to 125 | QTL905 | Samples |

(1) The marketing status values are defined as follows:
**ACTIVE:** Product device recommended for new designs.
**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.
**OBSOLETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

**OTHER QUALIFIED VERSIONS OF TLV9051-Q1, TLV9052-Q1 :**

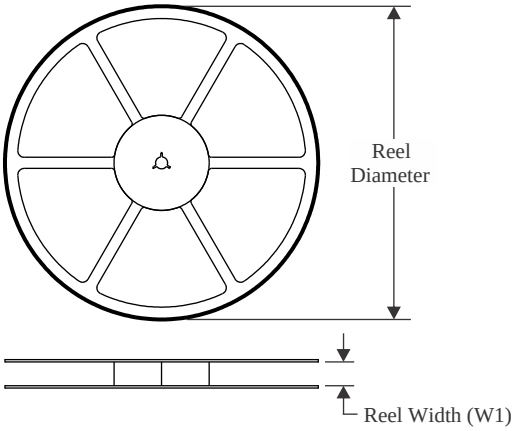
- Catalog : TLV9051, TLV9052

NOTE: Qualified Version Definitions:

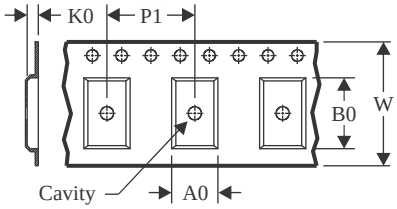
- Catalog - TI's standard catalog product

## TAPE AND REEL INFORMATION

**REEL DIMENSIONS**

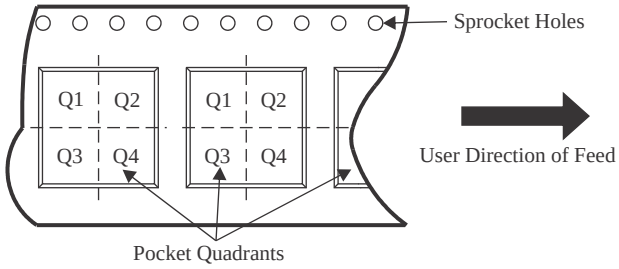



**TAPE DIMENSIONS**




| | |
|---|---|
| A0 | Dimension designed to accommodate the component width |
| B0 | Dimension designed to accommodate the component length |
| K0 | Dimension designed to accommodate the component thickness |
| W | Overall width of the carrier tape |
| P1 | Pitch between successive cavity centers |

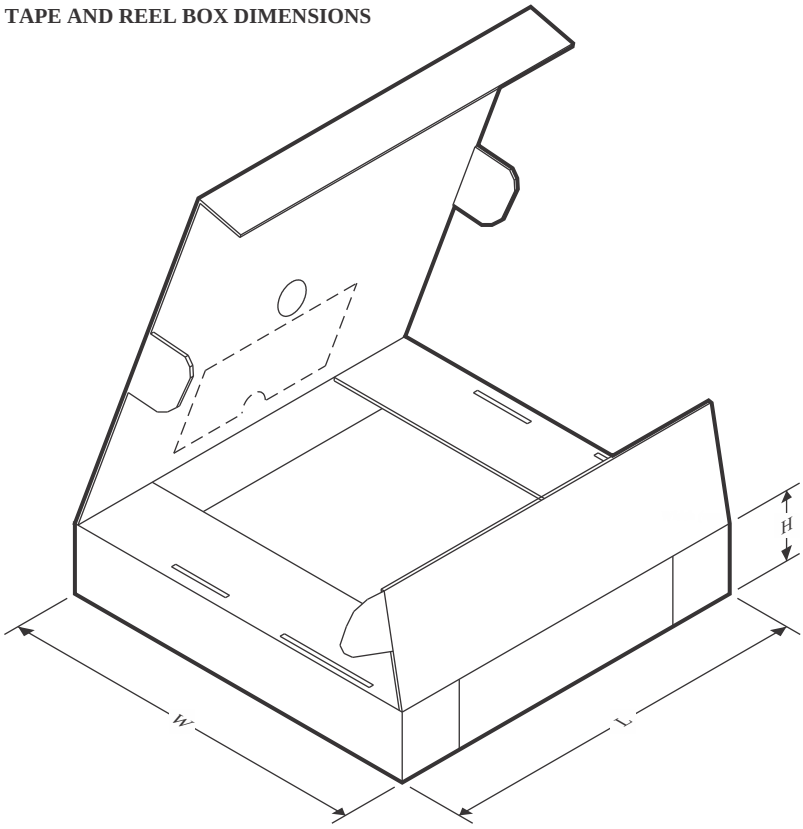
**QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE**




*All dimensions are nominal

| Device | Package Type | Package Drawing | Pins | SPQ | Reel Diameter (mm) | Reel Width W1 (mm) | A0 (mm) | B0 (mm) | K0 (mm) | P1 (mm) | W (mm) | Pin1 Quadrant |
|---|---|---|---|---|---|---|---|---|---|---|---|---|
| TLV9051QDBVRQ1 | SOT-23 | DBV | 5 | 3000 | 180.0 | 8.4 | 3.2 | 3.2 | 1.4 | 4.0 | 8.0 | Q3 |
| TLV9052QPWRQ1 | TSSOP | PW | 8 | 3000 | 330.0 | 12.4 | 7.0 | 3.6 | 1.6 | 8.0 | 12.0 | Q1 |

TAPE AND REEL BOX DIMENSIONS




*All dimensions are nominal

| Device | Package Type | Package Drawing | Pins | SPQ | Length (mm) | Width (mm) | Height (mm) |
|---|---|---|---|---|---|---|---|
| TLV9051QDBVRQ1 | SOT-23 | DBV | 5 | 3000 | 210.0 | 185.0 | 35.0 |
| TLV9052QPWRQ1 | TSSOP | PW | 8 | 3000 | 353.0 | 353.0 | 32.0 |

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